

ZXTN23015CFH

15V, SOT23, NPN medium power transistor

Summary

$V_{(BR)CEX} > 60V, V_{(BR)CEO} > 15V$

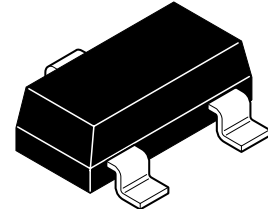
$I_{C(CONT)} = 6A$

$R_{CE(SAT)} = 19m\Omega$ typical

$V_{CE(SAT)} < 30mV @ 1A$

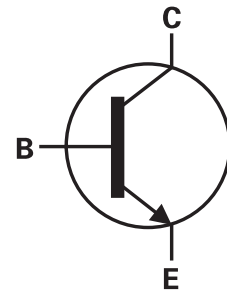
$P_D = 1.25W$

Complementary part number : ZXTP23015CFH



Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

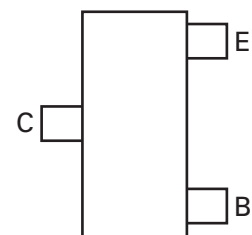


Features

- Higher power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 60V forward blocking voltage

Applications

- DC - DC converters
- MOSFET and IGBT gate driving
- Motor drive
- Relay, lamp, and solenoid drive



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width	Quantity per REEL
ZXTN23015CFHTA	7	8mm	3000

Device marking

327

ZXTN23015CFH

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	$V_{(BR)CEX}$	60	V
Collector-emitter voltage	V_{CEO}	15	V
Emitter-base voltage	V_{EBO}	7.0	V
Peak pulse current	I_{CM}	12	A
Continuous collector current ^(c)	I_C	6	A
Base current	I_B	1.2	A
Power dissipation @ $T_A=25^{\circ}C^{(a)}$ Linear derating factor ^(a)	P_D	0.73 5.84	W mW/ $^{\circ}C$
Power dissipation @ $T_A=25^{\circ}C^{(b)}$ Linear derating factor ^(b)	P_D	1.05 8.4	W mW/ $^{\circ}C$
Power dissipation @ $T_A=25^{\circ}C^{(c)}$ Linear derating factor ^(c)	P_D	1.25 9.6	W mW/ $^{\circ}C$
Power dissipation @ $T_A=25^{\circ}C^{(d)}$ Linear derating factor ^(d)	P_D	1.81 14.5	W mW/ $^{\circ}C$
Operating and storage temperature	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

Thermal resistance

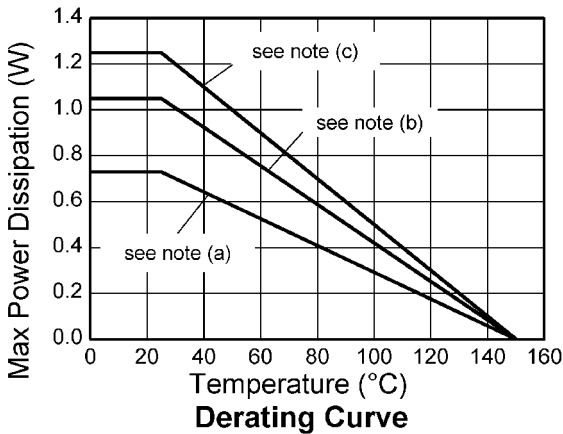
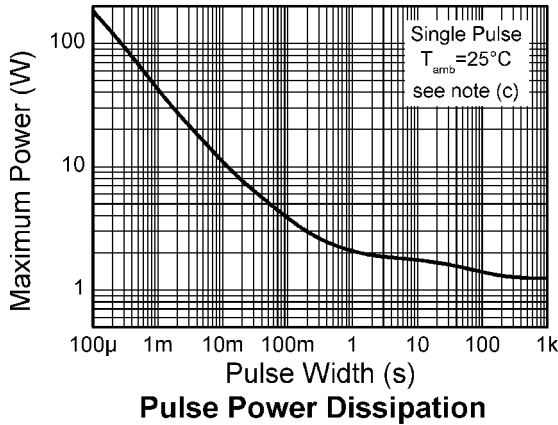
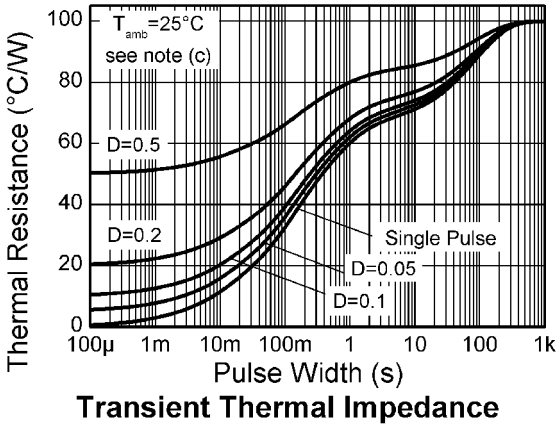
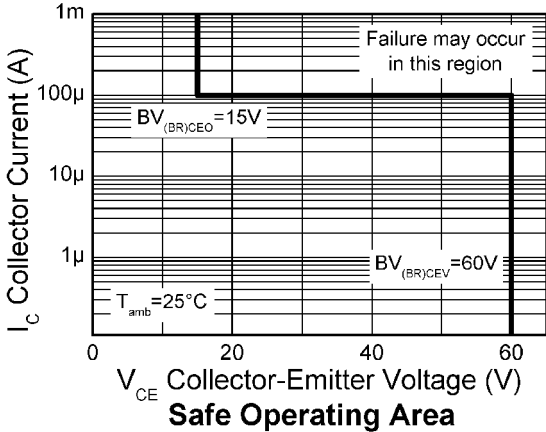
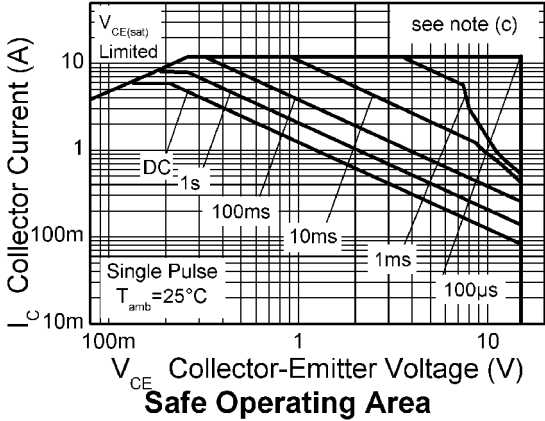
Parameter	Symbol	Value	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	171	$^{\circ}C/W$
Junction to ambient ^(b)	$R_{\theta JA}$	119	$^{\circ}C/W$
Junction to ambient ^(c)	$R_{\theta JA}$	100	$^{\circ}C/W$
Junction to ambient ^(d)	$R_{\theta JA}$	69	$^{\circ}C/W$

NOTES:

- (a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
- (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.
- (d) As (c) above measured at $t < 5$ secs.

ZXTN23015CFH

Characteristics



ZXTN23015CFH

Electrical characteristics (at $T_{AMB} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}$	60	85		V	$I_C = 100\mu\text{A}$
Collector-emitter breakdown voltage	$V_{(BR)CEX}$	60	85		V	$I_C = 100\mu\text{A}$, $R_{BE} \leq 1\text{k}\Omega$ OR $-1\text{V} < V_{BE} < 0.25\text{V}$
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	15	23		V	$I_C = 10\text{mA}^{(*)}$
Emitter-base breakdown voltage	$V_{(BR)EBO}$	7.0	8.3		V	$I_E = 100\mu\text{A}$
Collector-emitter cut-off current	I_{CEX}		-	100	nA	$V_{CE} = 48\text{V}$, $R_{BE} \leq 1\text{k}\Omega$ OR $-1\text{V} < V_{BE} < 0.25\text{V}$
Collector-base cut-off current	I_{CBO}		<1	20	nA	$V_{CB} = 48\text{V}$
Emitter-base cut-off current	I_{EBO}		<1	10	nA	$V_{EB} = 6\text{V}$
Static forward current transfer ratio	H_{FE}	160 200 190 150	300 350 330 280	560		$I_C = 10\text{mA}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 500\text{mA}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 3\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 6\text{A}$, $V_{CE} = 2\text{V}^{(*)}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		7 22 70 130	15 30 90 180	mV	$I_C = 0.1\text{A}$, $I_B = 5\text{mA}^{(*)}$ $I_C = 1\text{A}$, $I_B = 100\text{mA}^{(*)}$ $I_C = 3\text{A}$, $I_B = 60\text{mA}^{(*)}$ $I_C = 6\text{A}$, $I_B = 120\text{mA}^{(*)}$
Base-emitter saturation voltage	$V_{BE(sat)}$		0.83 0.89	0.93 0.98	V	$I_C = 3\text{A}$, $I_B = 60\text{mA}^{(*)}$ $I_C = 6\text{A}$, $I_B = 120\text{mA}^{(*)}$
Base-emitter turn-on voltage	$V_{BE(on)}$		0.81	0.91	V	$I_C = 6\text{A}$, $V_{CE} = 2\text{V}^{(*)}$
Transition frequency	f_T		235		MHz	$I_C = 500\text{mA}$, $V_{CE} = 2\text{V}$, $f = 50\text{MHz}$
Output capacitance	C_{obo}		56		pF	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}$
Delay time	$t_{(d)}$		15		ns	$V_{CC} = 5\text{V}$, $I_C = 3\text{A}$, $I_{B1} = I_{B2} = 150\text{mA}$
Rise time	$t_{(r)}$		38.5		ns	
Storage time	$t_{(stg)}$		213		ns	
Fall time	$t_{(f)}$		19.7		ns	

NOTES:

(*) Measured under pulsed conditions. Pulse width = $300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical characteristics

